

This Page Is Inserted by IFW Operations
and is not a part of the Official Record

BEST AVAILABLE IMAGES

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

IMAGES ARE BEST AVAILABLE COPY.

**As rescanning documents *will not* correct images,
please do not report the images to the
Image Problem Mailbox.**

L Number	Hits	Search Text	DB	Time stamp
1	1672	118/719.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:14
2	2090	29/25.01.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:07
3	333	427/9.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:07
4	6936	438/5-18.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:07
5	2423	700/19,49,52,99-104,108-111,119-121,123.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:08
6	894	L1-L5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:08
7	13149	118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:08
8	1237213	((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or making))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:39
9	7683	(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or making)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:40
10	1146265	((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:41
11	5313	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or making)))) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:16

12	1860420	((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:44
13	4526	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or making)))) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3)))) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:23
14	1069	700/19,49,52,99-104,108-111,119-121,123.ccls. and (((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or making)))) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3)))) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:23
15	560847	((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:40
16	6256	(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:40
17	2140	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or processor) with (deposit\$3 or etch\$3 or metrology or measur\$3 or polish\$3 or lithography or exposure or oxidation or oxidizing or implant\$5 or planariz\$5 or CVD or vapor-deposit\$3 or chemical-vapor or clean\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:50

18	873	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and'(((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or processor) with (deposit\$3 or etch\$3 or metrology or measur\$3 or polish\$3 or lithography or exposure or oxidation or oxidizing or implant\$5 or planariz\$5 or CVD or vapor-deposit\$3 or chemical-vapor or clean\$3))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:03
19	113	700/19,49,52,99-104,108-111,119-121,123.ccls. and (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or processor) with (deposit\$3 or etch\$3 or metrology or measur\$3 or polish\$3 or lithography or exposure or oxidation or oxidizing or implant\$5 or planariz\$5 or CVD or vapor-deposit\$3 or chemical-vapor or clean\$3))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:45
20	1804	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or processor) with (deposit\$3 or etch\$3 or metrology or measur\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:50
21	581	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or processor) with (deposit\$3 or etch\$3 or metrology or measur\$3))) and (chamber near5 (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:51
22	263	(((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or processor) with (deposit\$3 or etch\$3 or metrology or measur\$3))) and (chamber near5 (((process\$3 or cycle or average or mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5))) and (@pd<=20000813)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:10
23	439	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:37
24	167	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (@pd<=20000813)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:37

25	23	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (@pd<=20000813)) and (software)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:34
26	272	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) not (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (@pd<=20000813))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:34
27	55	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) not (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (@pd<=20000813)) and (applied adj materials).as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:37
28	513	(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:51
29	78	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:37
30	23	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) and (@pd<=20000813)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:37

31	55	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) not (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) and (@pd<=20000813)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:38
32	55	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) not (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) and (@pd<=20000813))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3))))).clm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:23
33	12	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) not (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) and (@pd<=20000813))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3))))).clm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:52
38	55	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) not (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) and (@pd<=20000813))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:24

39	1582	(chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:28
40	74	((chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm.) and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:31
41	54	(chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm. and software	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:31
42	18	(chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm. and software) and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:31
43	153	(chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:31
45	36	((chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm. and software) not ((chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm. and software) and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:32
44	25	((chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm.) and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:46
46	7	((chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm.) and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) not ((chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber))))).clm. and software)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 22:46
-	2	20030029383.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 20:06